Emmanouil Dimakis

List of Publications by Year
in descending order

31 papers	755 citations	516710 16 h-index	526287 27 g-index
31 all docs	31 docs citations	31 times ranked	1025 citing authors

#	Article	IF	Citations
1	High-field charge transport in InGaAs nanowires. , 2021, , .		0
2	High electron mobility in strained GaAs nanowires. Nature Communications, 2021, 12, 6642.	12.8	28
3	Nonlinear Charge Transport in InGaAs Nanowires at Terahertz Frequencies. Nano Letters, 2020, 20, 3225-3231.	9.1	12
4	All-THz pump-probe spectroscopy of the intersubband AC-Stark effect in a wide GaAs quantum well. Optics Express, 2020, 28, 25358.	3.4	2
5	Nonlinear plasmonic response in GaAs/InGaAs core/shell nanowires. , 2020, , .		0
6	Pump â€“ probe THz spectroscopy study of electronic properties of semiconductor nanowires. , 2019, , .		1
7	Broadband Photo-Excited Coherent Acoustic Frequency Combs and Mini-Brillouin-Zone Modes in a MQW-SESAM Structure. Applied Sciences (Switzerland), 2019, 9, 289.	2.5	7
8	Widely tunable GaAs bandgap via strain engineering in core/shell nanowires with large lattice mismatch. Nature Communications, 2019, 10, 2793.	12.8	78
9	Electron dynamics in In_xGa_{1â^'x}As shells around GaAs nanowires probed by terahertz spectroscopy. Nanotechnology, 2019, 30, 244004.	2.6	9
10	Plasmonic nonlinearity in GaAs/In0.20Ga0.80As core/shell nanowires. , 2019, , .		0
11	Nonlinear plasmonic response of doped nanowires observed by infrared nanospectroscopy. Nanotechnology, 2019, 30, 084003.	2.6	10
12	A simple route to synchronized nucleation of self-catalyzed GaAs nanowires on silicon for sub-Poissonian length distributions. Nanotechnology, 2018, 29, 504004.	2.6	15
13	Decoupling the Two Roles of Ga Droplets in the Self-Catalyzed Growth of GaAs Nanowires on SiO_x/Si(111) Substrates. Crystal Growth and Design, 2017, 17, 5276-5282.	3.0	26
14	How Indium Nitride Senses Water. Nano Letters, 2017, 17, 7339-7344.	9.1	18
15	Droplet-Confined Alternate Pulsed Epitaxy of GaAs Nanowires on Si Substrates down to CMOS-Compatible Temperatures. Nano Letters, 2016, 16, 4032-4039.	9.1	20
16	Correlation of Electrical and Structural Properties of Single As-Grown GaAs Nanowires on Si (111) Substrates. Nano Letters, 2015, 15, 981-989.	9.1	29
17	Polytypism in GaAs nanowires: determination ofÂthe interplanar spacing of wurtzite GaAs by X-ray diffraction. Journal of Synchrotron Radiation, 2015, 22, 67-75.	2.4	17
18	Plan-view transmission electron microscopy investigation of GaAs/(In,Ga)As core-shell nanowires. Applied Physics Letters, 2014, 105, 121602.	3.3	16

#	Article	IF	Citations
19	Role of Liquid Indium in the Structural Purity of Wurtzite InAs Nanowires That Grow on Si(111). Nano Letters, 2014, 14, 6878-6883.	9.1	27
20	Coaxial Multishell (In,Ga)As/GaAs Nanowires for Near-Infrared Emission on Si Substrates. Nano Letters, 2014, 14, 2604-2609.	9.1	111
21	Impact of strain induced by polymer curing in benzocyclobutene embedded semiconductor nanostructures. Physica Status Solidi - Rapid Research Letters, 2014, 8, 1007-1010.	2.4	1
22	In situ doping of catalyst-free InAs nanowires with Si: Growth, polytypism, and local vibrational modes of Si. Applied Physics Letters, 2013, 103, .	3.3	15
23	Plasmonic off-axis unidirectional beaming of quantum-well luminescence. Applied Physics Letters, 2013, 103, .	3.3	18
24	Plasmon-enhanced light emission based on lattice resonances of silver nanocylinder arrays. Optics Letters, 2012, 37, 79.	3.3	42
25	Shell-doping of GaAs nanowires with Si for n-type conductivity. Nano Research, 2012, 5, 796-804.	10.4	42
26	Self-Assisted Nucleation and Vaporâ€“Solid Growth of InAs Nanowires on Bare Si(111). Crystal Growth and Design, 2011, 11, 4001-4008.	3.0	95
27	Enhanced near-green light emission from InGaN quantum wells by use of tunable plasmonic resonances in silver nanoparticle arrays. Optics Express, 2010, 18, 21322.	3.4	69
28	Plasmon enhanced light emission from InGaN quantum wells via coupling to chemically synthesized silver nanoparticles. Applied Physics Letters, 2009, 95, 151109.	3.3	30
29	Nonlinear carrier recombination and transport features in highly excited InN layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S735-S738.	0.8	6
30	Femtosecond time-resolved study in InxGa1â^'xN (0001) ultrathin epilayers: Effects of high indium mole fraction and thickness of the films. Applied Physics Letters, 2006, 89, 241109.	3.3	1
31	Ultrafast carrier dynamics in InxGa1â^'xN (0001) epilayers: Effects of high fluence excitation. Applied Physics Letters, 2006, 88, 121128.	3.3	10